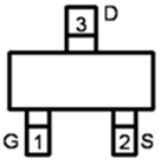
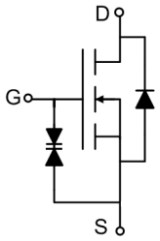
Main Product Characteristics:

V_{DSS}	60V
R_{DS}(on)	1.69Ω(typ.)
I_D	0.3A

SOT-23



Pin Assignments



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- ESD Rating：2000V HBM
- AEC-Q101 qualified

Description:

It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

Absolute Max Rating:

Symbol	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V①	0.3	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V①	0.2	
I_{DM}	Pulsed Drain Current②	1.2	
P_D @T_C = 25°C	Power Dissipation③	0.35	W
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-to-Source Voltage	± 20	V
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C

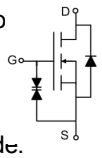
Thermal Resistance

Symbol	Characterizes	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient④	—	357	℃/W

Electrical Characterizes @T_A=25℃unless otherwise specified

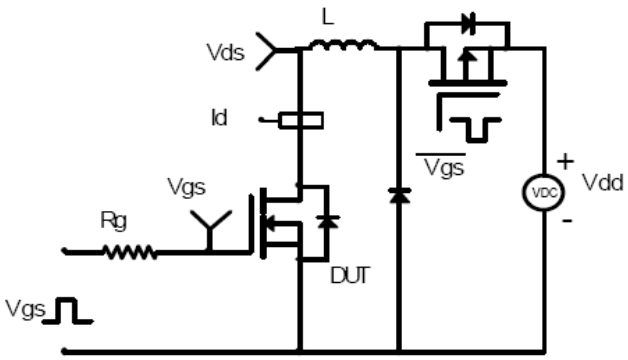
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	60	—	—	V	V_{GS} = 0V, I_D = 250μA
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	1.69	2.2	Ω	V_{GS}=10V, I_D=0.3A
		—	2.05	2.87	Ω	V_{GS}=4.5V, I_D=0.2A
$V_{GS(th)}$	Gate threshold voltage	1	—	2.5	V	V_{DS}=V_{GS},I_D=250μA
I_{DSS}	Drain-to-Source leakage current	—	—	1	μA	V_{DS}=60V,V_{GS}=0V
I_{GSS}	Gate-to-Source forward leakage	—	—	±10	μA	V_{GS}=±20V,V_{DS}=0V
Q_g	Total gate charge	—	1.7	—	nC	I_D =0.3A, V_{DS}=10V, V_{GS} =4.5V
Q_{gs}	Gate-to-Source charge	—	0.3	—		
Q_{gd}	Gate-to-Drain("Miller") charge	—	0.6	—		
$t_{d(on)}$	Turn-on delay time	—	3.8	—	ns	V_{DD}=20V, V_{GS}=10V, R_{GEN}=10Ω， R_L=100Ω I_D=0.2A
t_r	Rise time	—	5.4	—		
$t_{d(off)}$	Turn-Off delay time	—	8.4	—		
t_f	Fall time	—	3.2	—		
C_{iss}	Input capacitance	—	15	—	pF	V_{DS}=50V, V_{GS}=0V, f=1.0MHz
C_{oss}	Output capacitance	—	6	—		
C_{rss}	Reverse transfer capacitance	—	1.5	—		

Source-Drain Ratings and Characteristics

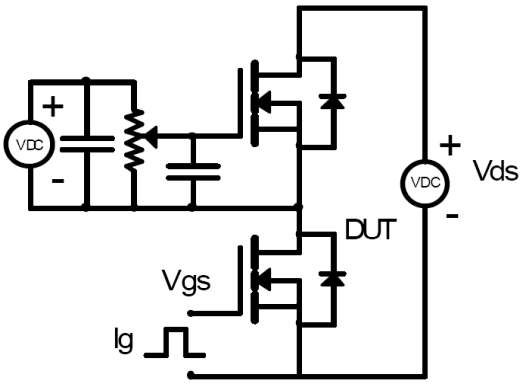
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	0.3	A	MOSFET symbo showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode)	—	—	1.2	A	
V_{SD}	Diode Forward Voltage	—	—	1.2	V	V_{GS}=0V,I_S=0.3A

Test Circuits and Waveforms

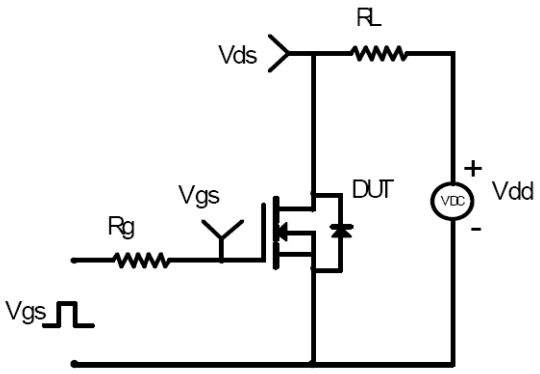
EAS Test Circuit:



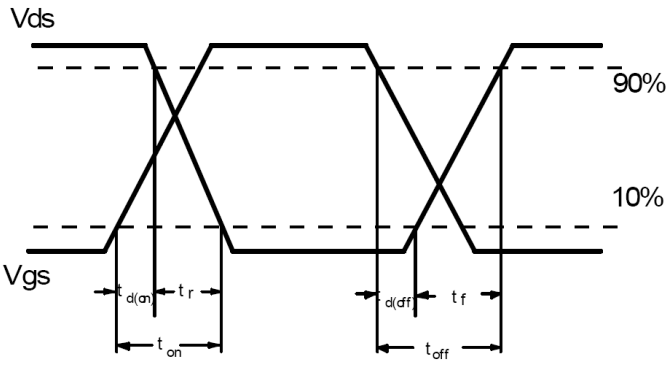
Gate Charge Test Circuit:



Switching Time Test Circuit:



Switching Waveforms:



Notes:

① Calculated continuous current based on maximum allowable junction temperature.
② Repetitive rating; pulse width limited by max. junction temperature.
③ The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.
④ The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25 ℃

Typical Electrical and Thermal Characteristics

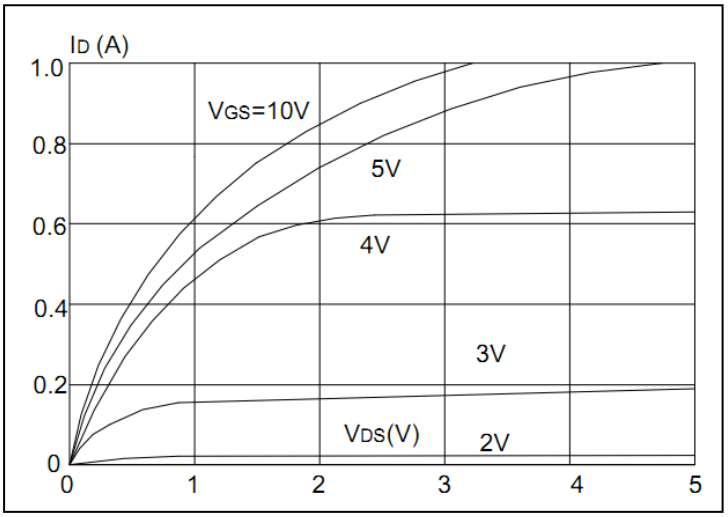


Figure1.Typical Output Characteristics

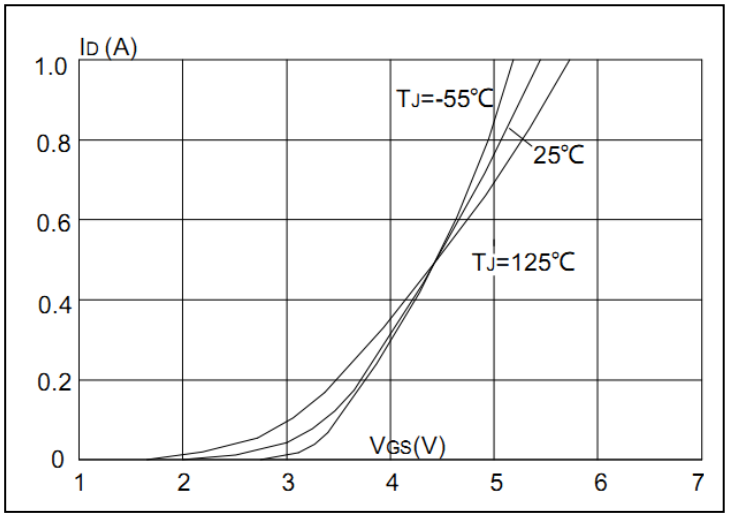


Figure2. Typical Transfer Characteristics

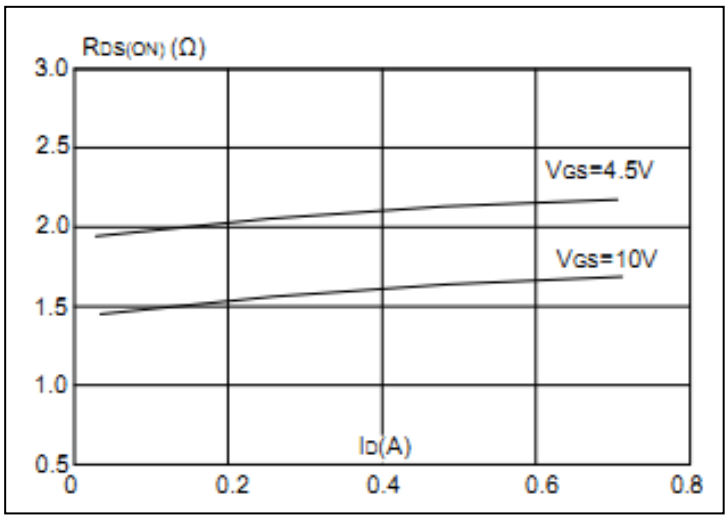


Figure3. On-Resistance vs. Drain Current

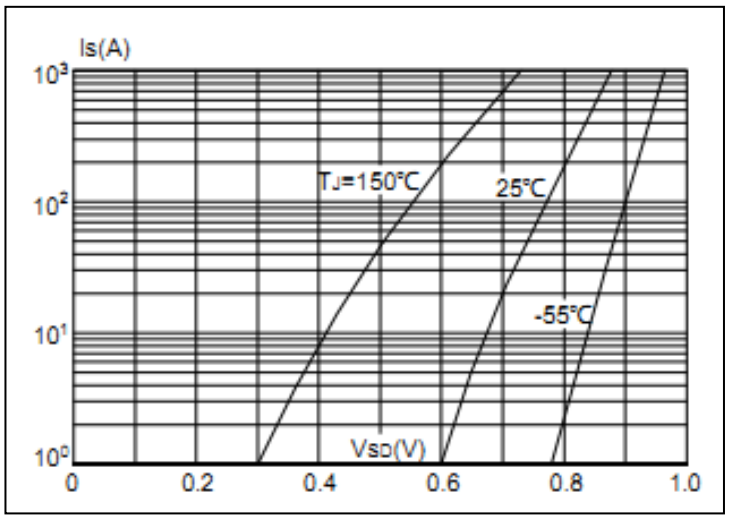


Figure4. Body Diode Characteristics

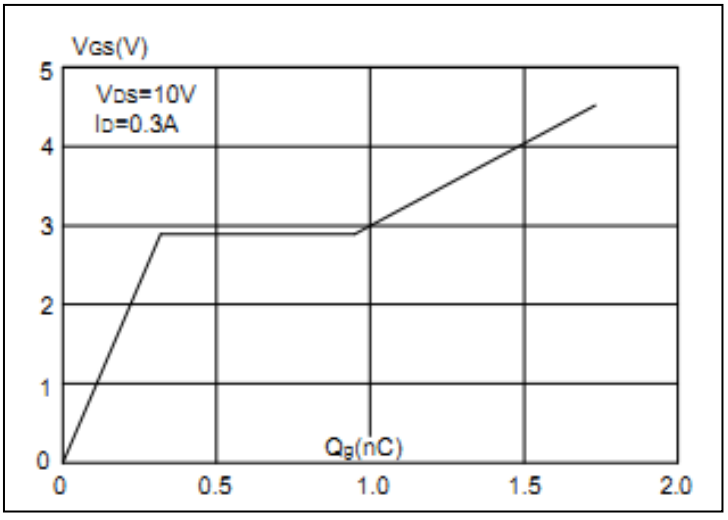


Figure5. Gate Charge Characteristics

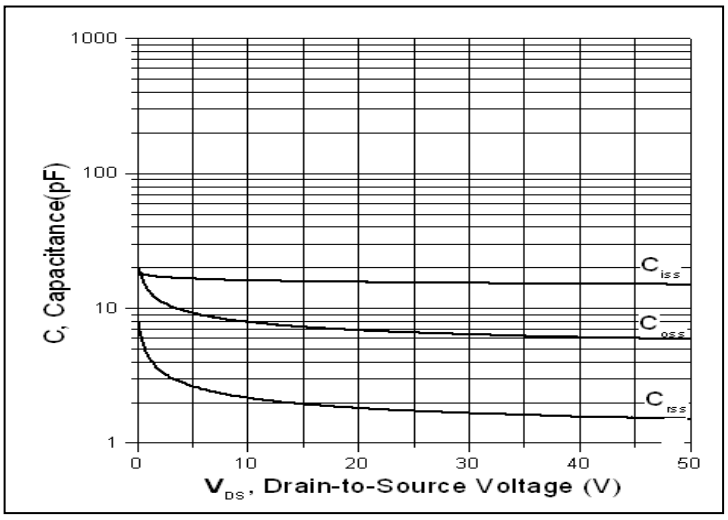


Figure6. Capacitance Characteristics

Typical Electrical and Thermal Characteristics

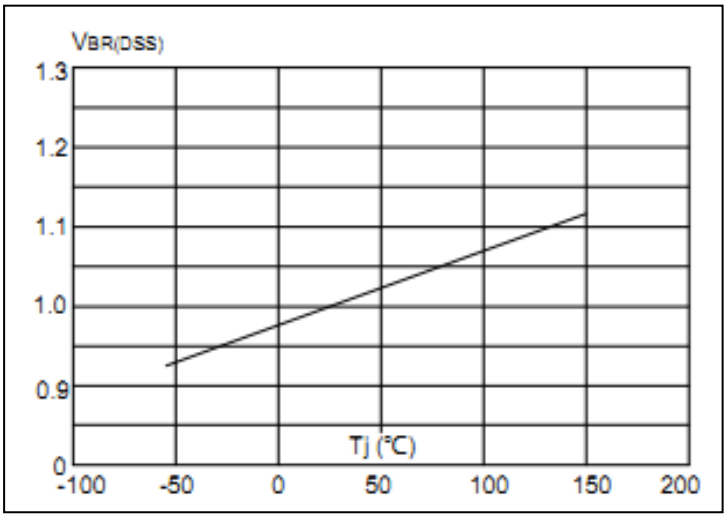


Figure7. Normalized Breakdown Voltage vs. Junction Temperature

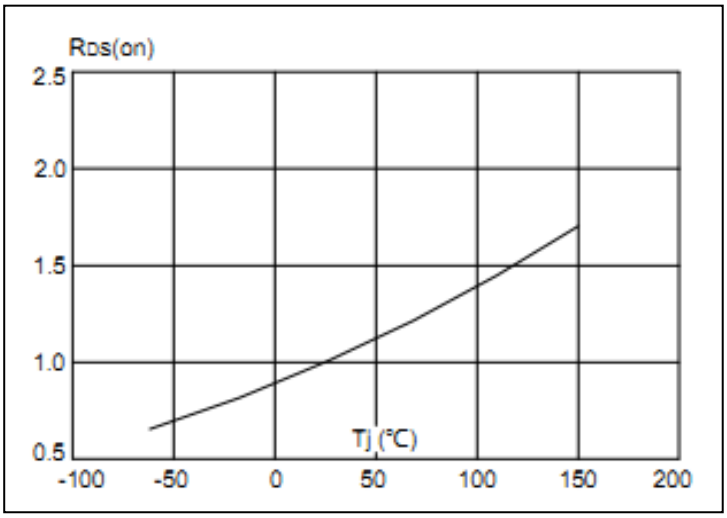


Figure8. Normalized On-Resistance vs. Junction Temperature

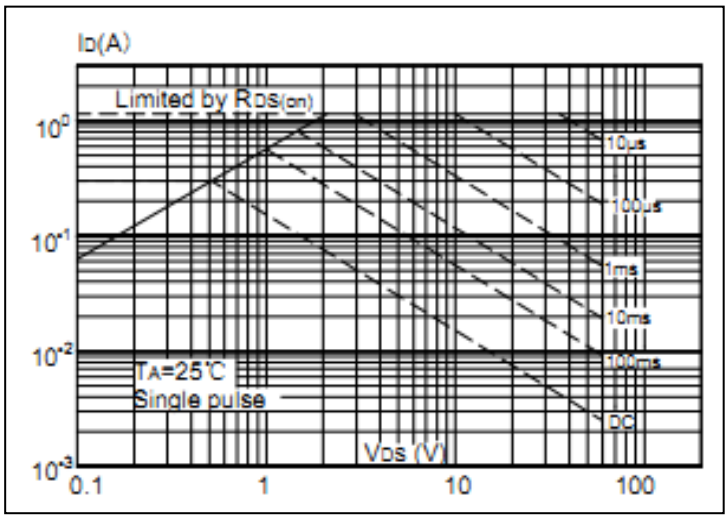


Figure9. Maximum Safe Operation Area

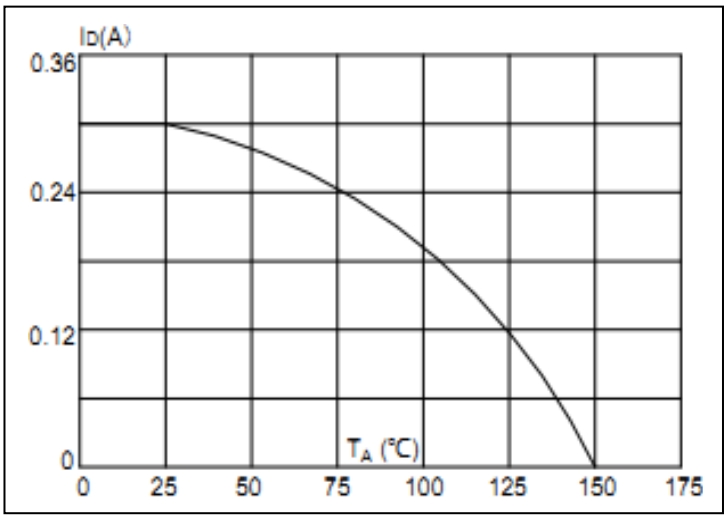


Figure10. Maximum Continuous Drain Current vs. Ambient Temperature

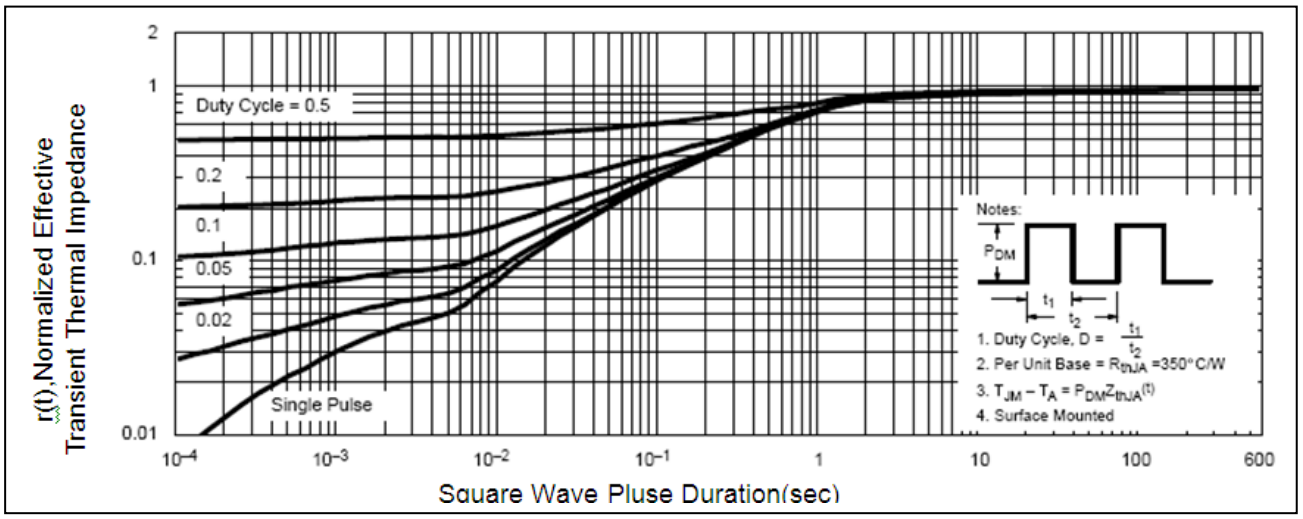
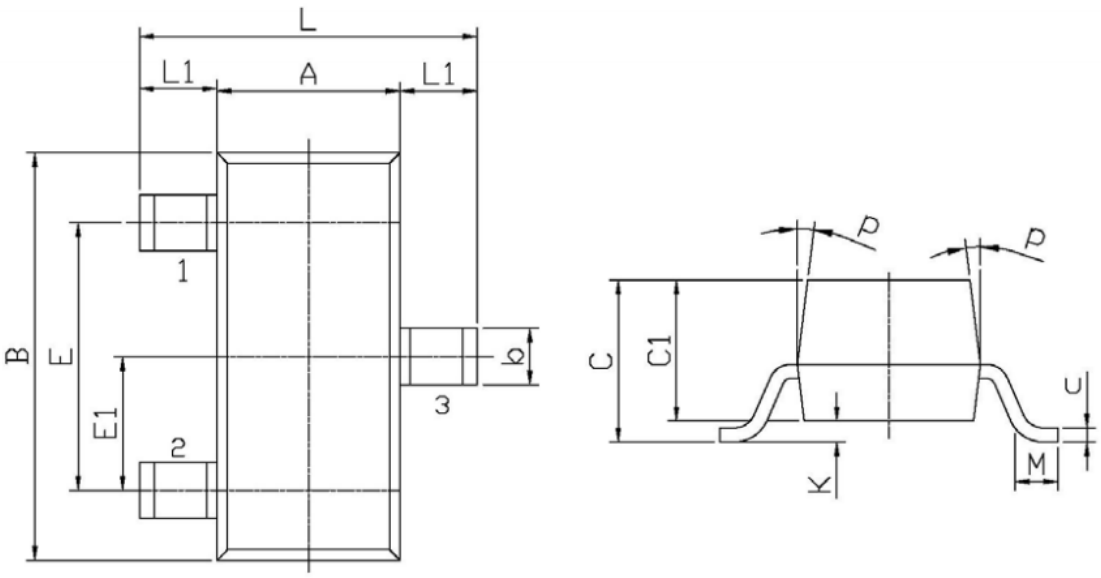


Figure11. Normalized Maximum Transient Thermal Impedance

Mechanical Data：

SOT-23 Package Outline(Unit:mm)



Symbol	Dimensions in Millimeter		Symbol	Dimensions in Millimeter	
	Min	Max		Min	Max
L	2.2	2.7	C	1.30 Max	
L1	0.45	0.65	C1	0.90	1.20
A	1.15	1.50	c	0.05	0.20
B	2.70	3.10	K	0	0.10
E	1.70	2.10	M	0.20 Min	
E1	0.85	1.05	P	7°	
b	0.35	0.55			

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